RC4558, RC4558Y, RM4558, RV4558 DUAL HIGH-PERFORMANCE OPERATIONAL AMPLIFIERS

SLOS073 - MARCH 1976 - REVISED AUGUST 1991

- Continuous-Short-Circuit Protection
- Wide Common-Mode and Differential Voltage Ranges
- No Frequency Compensation Required
- Low Power Consumption
- No Latch-Up
- Unity Gain Bandwidth . . . 3 MHz Typ
- Gain and Phase Match Between Amplifiers
- Low Noise . . . 8 nV√Hz Typ at 1 kHz
- Designed To Be Interchangeable With Raytheon RC4558, RM4558, and RV4558

description

The RC4558, RM4558, and RV4558 are dual high-performance operational amplifiers with each half electrically similar to the μA741 except that offset null capability is not provided.

The high common-mode input voltage range and the absence of latch-up make these amplifiers ideal for voltage-follower applications. The devices are short-circuit protected and the internal frequency compensation ensures stability without external components.

The RC4558 is characterized for operation from 0° C to 70° C, the RM4558 is characterized for operation over the full military temperature range of -55° C to 125° C, and the RV4558 is characterized for operation from -40° C to 85° C.

AVAILABLE OPTIONS

TA	V _{IO} max	PACKAGED DEVICES							
	AT 25°C	SMALL OUTLINE (D)	SSOP (DBLE)	CERAMIC DIP (JG)	PLASTIC DIP (P)	SSOP (PWLE)	CHIP FORM (Y)		
0°C to 70°C	6 mV	RC4558D	RC4558DBLE	_	RC4558P	RC4558PWLE	RC4558Y		
−40°C to 85°C	6 mV	RV4558D	_		RV4558P	_			
−55°C to 125°C	6 mV	_	_	RM4558JG	_	_	_		

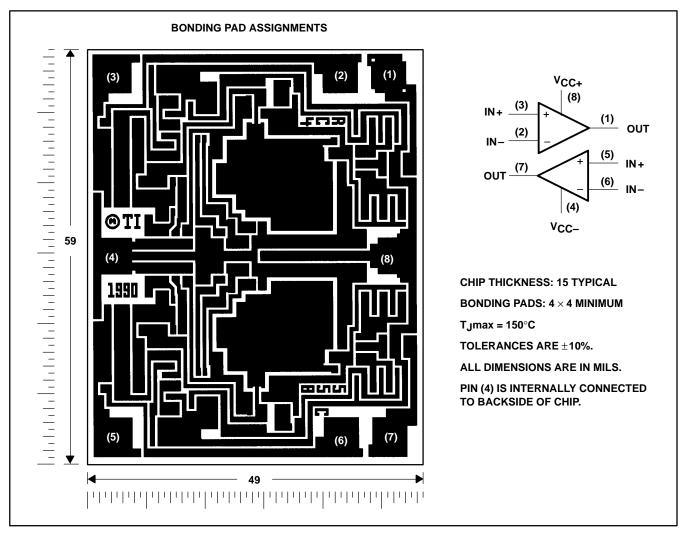
The D package is available taped and reeled. Add the suffix R to the device type (e.g., RC4558DR). The DB and PW packages are available only left-end taped and reeled. RC4558Y is tested at 25°C.



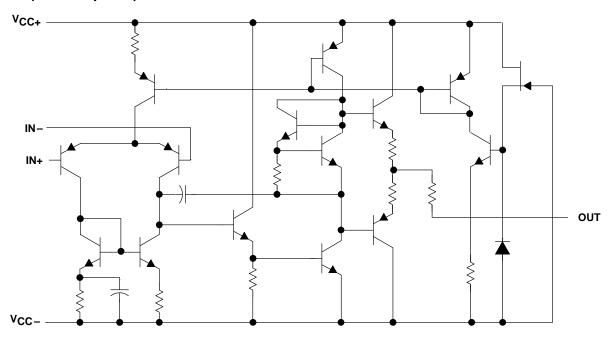
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RC4558Y chip information

These chips, properly assembled, display characteristics similar to the RC4558. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.



schematic (each amplifier)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

	RC4558	RM4558	RV4558	UNIT	
Supply voltage V _{CC+} (see Note 1)	18	22	18	V	
Supply voltage V _{CC} (see Note 1)	-18	-22	-18	V	
Differential input voltage (see Note 2)	±30	±30	±30	V	
Input voltage (any input, see Notes 1 and 3)	±15	±15	±15	V	
Duration of output short circuit to ground, one amplifier at a time (see Note 4)	unlimited	unlimited	unlimited		
Continuous total dissipation	See Dissipation Rating Table				
Operating free-air temperature range	0 to 70	-55 to 125	-40 to 85	°C	
Storage temperature range	-65 to 150	-65 to 150	-65 to 150	°C	
Lead temperature 1,6 mm (1/16 inch) from case for 60 seconds: JG package		300		°C	
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: D, DB, P, or PW package	260		260	°C	

NOTES: 1. All voltage values, unless otherwise noted, are with respect to the midpoint between V_{CC+} and V_{CC-} .

- 2. Differential voltages are at IN+ with respect to IN-.
- 3. The magnitude of the input voltage must never exceed the magnitude of the supply voltage or 15 V, whichever is less.
- 4. Temperature and/or supply voltages must be limited to ensure that the dissipation rating is not exceeded.

DISSIPATION RATING TABLE

PACKAGE	$T_{\mbox{\scriptsize A}} \le 25^{\circ}\mbox{\scriptsize C}$ POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	DERATE ABOVE T _A	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING	T _A = 125°C POWER RATING
D	680 mW	5.8 mW/°C	33°C	464 mW	377 mW	N/A
DB or PW	525 mW	4.2 mW/°C	25°C	336 mW	N/A	N/A
JG	680 mW	8.4 mW/°C	69°C	672 mW	546 mW	210 mW
Р	680 mW	8.0 mW/°C	65°C	640 mW	520 mW	N/A

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recommended operating conditions

	MIN	MAX	UNIT
Supply voltage, V _{CC+}	5	15	V
Supply voltage, V _{CC} _	-5	-15	V

electrical characteristics at specified free-air temperature, $V_{CC+} = 15 \text{ V}$, $V_{CC-} = -15 \text{ V}$

DADAMETO		TEST CONDITIONS†		F	RC4558		RM4558			RV4558			UNIT
	PARAMETR	I EST CONL	DITIONS	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNII
V _{IO}	Input offset voltage	V _O = 0	25°C		0.5	6		0.5	5		0.5	6	mV
VΙΟ	input onset voltage	vO = 0	Full range			7.5			6			7.5	IIIV
l	Input offset current	V _O = 0	25°C		5	200		5	200		5	200	nA
I _{IO}	input onset current	vO = 0	Full range			300			500			500	IIA
1	Input bias current	V _O = 0	25°C		150	500		140	500		140	500	nA
I _{IB}	input bias current	v _O = 0	Full range			800			1500			1500	
V _{ICR}	Common-mode input voltage range		25°C	±12	±14		±12	±14		±12	±14		٧
		$R_L = 10 \text{ k}\Omega$	25°C	±12	±14		±12	±14		±12	±14		
V _{OM}	Maximum output voltage swing	$R_L = 2 k\Omega$	25°C	±10	±13		±10	±13		±10	±13		V
	voltago ovillig	$R_L \ge 2 \ k\Omega$	Full range	±10			±10			±10			7
Δ.	Large-signal differential	$R_L \ge 2 k\Omega$,	25°C	20	300		50	350		20	300		\//ma\/
A _{VD}	voltage amplification	$V_0 = \pm 10 \text{ V}$	Full range	15			25			15			V/mV
B ₁	Unity-gain bandwith		25°C		3		2	3.5			3		MHz
rį	Input resistance		25°C	0.3	5		0.3	5		0.3	5		MΩ
CMRR	Common-mode rejection ratio		25°C	70	90		70	90		70	90		dB
k _{SVS}	Supply voltage sensitivity (ΔV _{IO} /ΔV _{CC})	V _{CC} = ±15 V to ±9 V	25°C		30	150		30	150		30	150	μV/V
V _n	Equivalent input noise voltage (closed loop)	$A_{VD} = 100,$ $R_{S} = 100 \ \Omega,$ $f = 1 \ kHz,$ $BW = 1 \ Hz$	25°C		8			8			8		nV√ Hz
			25°C		2.5	5.6		2.5	5.6		2.5	5.6	
I _{CC}	Supply current (both amplifiers)	$V_O = 0$, No load	MIN T _A		3	6.6		3	6.6		3	6.6	mA
	ap	1.0.000	MAX T _A		2.3	5		2	5		2.3	5	
	-	., .	25°C		75	170		75	170		75	170	
P_D	Total power dissipation (both amplifiers)	V _O = 0, No load	MIN T _A		90	200		90	200		90	200	mW
	(= = 		MAX T _A		70	150		60	150		70	150	
V _{O1} /V _{O2}	Crosstalk Open loop	$R_S = 1 k\Omega$,	25°C		85			85			85		dB
VO1/ VO2	attenuation $A_{VD} = 100$	f = 10 kHz	23 0		105			105			105		GD.

[†] All characteristics are measured under open-loop conditions with zero common-mode input voltage unless otherwise specified. Full range is 0°C $to 70^{\circ}C for RC4558, -55^{\circ}C to 125^{\circ}C for RM4558, and -40^{\circ}C to 85^{\circ}C for RV4558. \\Minimum T_{A} is 0^{\circ}C for RC4558, -55^{\circ}C for RM4558, and -40^{\circ}C for RV4558. \\Minimum T_{A} is 0^{\circ}C for RC4558, -55^{\circ}C for RM4558, and -40^{\circ}C for RV4558. \\Minimum T_{A} is 0^{\circ}C for RC4558, -55^{\circ}C for RM4558, and -40^{\circ}C for RV4558. \\Minimum T_{A} is 0^{\circ}C for RC4558, -55^{\circ}C for RM4558, and -40^{\circ}C for RV4558. \\Minimum T_{A} is 0^{\circ}C for RC4558, -55^{\circ}C for RM4558, and -40^{\circ}C for RV4558. \\Minimum T_{A} is 0^{\circ}C for RC4558, -55^{\circ}C for RM4558, and -40^{\circ}C for RV4558. \\Minimum T_{A} is 0^{\circ}C for RC4558, -55^{\circ}C for RM4558, and -40^{\circ}C for RV4558. \\Minimum T_{A} is 0^{\circ}C for RC4558, -55^{\circ}C for RM4558, and -40^{\circ}C for RV4558. \\Minimum T_{A} is 0^{\circ}C for RC4558, -55^{\circ}C for RM4558, and -40^{\circ}C for RV4558. \\Minimum T_{A} is 0^{\circ}C for RC4558, -55^{\circ}C for RV4558, and -40^{\circ}C for RV4558. \\Minimum T_{A} is 0^{\circ}C for RV4558, -55^{\circ}C for RV4558, and -40^{\circ}C for RV4558. \\Minimum T_{A} is 0^{\circ}C for RV4558, -55^{\circ}C for RV4558, and -40^{\circ}C for RV4558, -55^{\circ}C fo$ for RV4558. Maximum T_A is 70°C for RC4558, 125°C for RM4558, and 85°C for RV4558.

operating characteristics, $V_{CC+} = 15 \text{ V}$, $V_{CC-} = -15 \text{ V}$, $T_A = 25^{\circ}\text{C}$

	PARAMETER		MIN	TYP	MAX	UNIT		
t _r	Rise time	V _I = 20 mV,	P 2 kO	C _I = 100 pF		0.13		ns
	Overshoot	ν = 20 mν,	$R_L = 2 k\Omega$,	CL = 100 pF		5%		
SR	Slew rate at unity gain	V _I = 10 V,	$R_L = 2 k\Omega$,	C _L = 100 pF	1.1	1.7		V/µs

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electrical characteristics, $V_{CC+} = 15 \text{ V}$, $V_{CC-} = -15 \text{ V}$, $T_A = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER				TEST CONDITIONS [†]			RC4558Y		
	PARAMETER		"	231 CONDITION	31	MIN	TYP	MAX 6 200 500 150 150 5.6	UNIT
V _{IO}	Input offset voltage		V _O = 0				0.5	6	mV
I _{IO}	Input offset current	VO = 0				5	200	nA	
I _{IB}	Input bias current		VO = 0				150	500	nA
VICR	Common-mode input voltage rang	е				±12	±14		V
V Madama adada la F		$R_L = 10 \text{ k}\Omega$			±12	±14		V	
VOM	Maximum output voltage swing		$R_L = 2 k\Omega$			±12	±13		
AVD	Large-signal differential voltage ar	$R_L = 2 k\Omega$,	V _O = ±10 V		20	300		V/mV	
B ₁	Unity-gain bandwidth						3		MHz
rį	Input resistance					0.3	5		МΩ
CMRR	Common-mode rejection ratio					70	90		dB
kSVS	Supply voltage sensitivity (ΔV _{IO} /Δ	V _{CC})	$V_{CC} = \pm 15 \text{ V to } \pm 9 \text{ V}$				30	150	μV/V
V _n	Equivalent input noise voltage (clo	sed-loop)	A _{VD} = 100, BW = 1 Hz	$R_S = 100 \Omega$,	f = 1 kHz,		8		nV√ Hz
ICC	Supply current (both amplifiers)		$V_{O} = 0$,	No load			2.5	5.6	mA
PD	Total power dissipation (both amp	V _O = 0,	No load			75	170	mW	
\/a./\/a	Open		D= 4 kC	f 10 kl l=			85		чD
VO1/VO2	Crosstalk attentuation	A _{VD} = 100	$R_S = 1 k\Omega$,	f = 10 kHz			105		dB

[†] All characteristics are measured under open-loop conditions with zero common-mode input voltage unless otherwise specified.

operating characteristics, V_{CC+} = 15 V, V_{CC-} = -15 V, T_A = 25°C

	PARAMETER		MIN	TYP	MAX	UNIT		
t _r	Rise time		C: - 100 pE		0.13		ns	
	Overshoot	ν ₁ = 20 πν,	$V_{\parallel} = 20 \text{ mV}, \qquad \qquad R_{\perp} = 2 \text{ k}\Omega, \qquad \qquad C_{\perp} = 100 \text{ pF}$			5%		
SR	Slew rate at unity gain	V _I = 10 V,	$R_L = 2 k\Omega$,	C _L = 100 pF	1.1	1.7		V/μs

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